

# **N-Channel Power MOSFET**

700V, 4.5A, 0.9Ω

### **FEATURES**

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

DI	IC	ΔΤΙ	ON

- Power Supply
- Lighting

KEY PERFORMANCE PARAMETERS					
PARAMETER VALUE UNIT					
V <sub>DS</sub>	700	V			
R <sub>DS(on)</sub> (max)	0.9	Ω			
$Q_g$	9.7	nC			



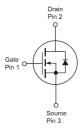












Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25°C unless otherwise noted)						
PARAMETER		SYMBOL	IPAK/DPAK	ITO-220	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	700		V	
Gate-Source Voltage		$V_{GS}$	±30		V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$		4.5 2.7		A	
	T <sub>C</sub> = 100°C	l <sub>D</sub>				
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	13.5		А	
Total Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>DTOT</sub>	50	20	W	
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	64		mJ	
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	1.6		А	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150		°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	IPAK/DPAK	ITO-220	UNIT	
Junction to Case Thermal Resistance	R <sub>eJC</sub>	2.5	6.25	°C/W	
Junction to Ambient Thermal Resistance	R <sub>OJA</sub>	62		°C/W	

**Notes:**  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\theta JA}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.  $R_{\theta JA}$  shown below for single device operation on FR-4 PCB in still air.





<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>C</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	700			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	2.0	3.1	4.0	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.5A$	R <sub>DS(on)</sub>		0.83	0.9	Ω
Dynamic (Note 5)						
Total Gate Charge	.,	$Q_g$		9.7		
Gate-Source Charge	$V_{DS} = 380V, I_{D} = 2.3A,$ $V_{GS} = 10V$	$Q_gs$		2.9		nC
Gate-Drain Charge	- V <sub>GS</sub> = 10V	$Q_{gd}$		3.5		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C <sub>iss</sub>		482		
Output Capacitance	f = 1.0MHz	C <sub>oss</sub>		34		pF
Gate Resistance	F = 1MHz, open drain	$R_g$		3.6		Ω
Switching (Note 6)						
Turn-On Delay Time		t <sub>d(on)</sub>		20		
Turn-On Rise Time	$V_{DD} = 380V,$ $R_{GEN} = 40\Omega,$ $I_{D} = 2.3A, V_{GS} = 10V,$	t <sub>r</sub>		54		
Turn-Off Delay Time		t <sub>d(off)</sub>		34		ns
Turn-Off Fall Time	1D - 2.3A, V <sub>GS</sub> - 10V,	t <sub>f</sub>		48		
Source-Drain Diode (Note 4)						
Forward On Voltage	I <sub>S</sub> = 4.5A, V <sub>GS</sub> = 0V	V <sub>SD</sub>			1.4	V
Reverse Recovery Time	V <sub>R</sub> =200V, I <sub>S</sub> = 2.3A	t <sub>rr</sub>		176		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q <sub>rr</sub>		1.1		μC

### Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 50mH,  $I_{AS} = 1.6A$ ,  $V_{DD} = 50V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$
- 4. Pulse test: PW  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.





### **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM70N900CI C0G	ITO-220	50pcs / Tube
TSM70N900CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM70N900CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

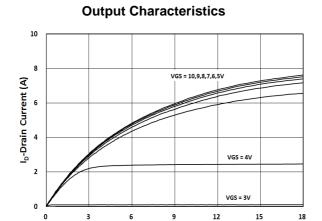
### Note:

- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



### **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 



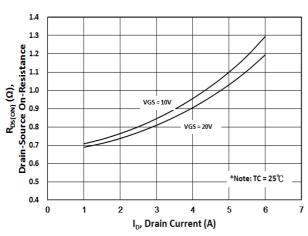
# 0.1 0 2 4 6 8 10 V<sub>GS</sub> Gate to Source Voltage

**Transfer Characteristics** 

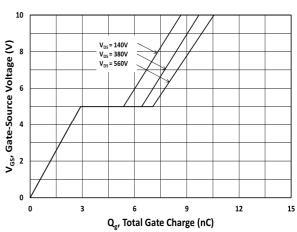
Vds = 10V



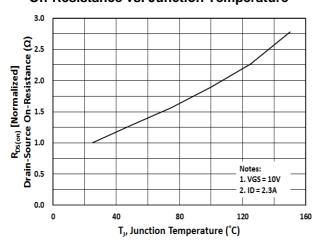
V<sub>DS</sub>-Drain to Source Voltage (V)



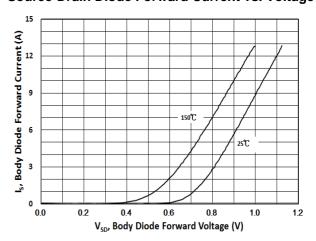
Gate-Source Voltage vs. Gate Charge



### **On-Resistance vs. Junction Temperature**



### Source-Drain Diode Forward Current vs. Voltage

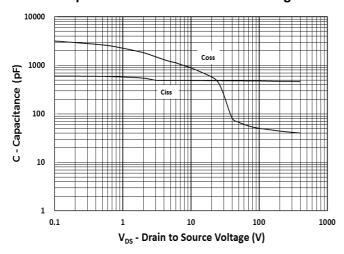




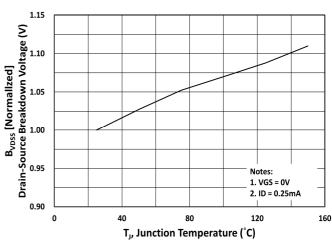
### **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

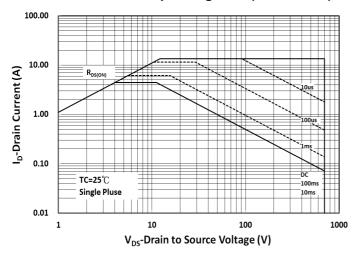
### Capacitance vs. Drain-Source Voltage



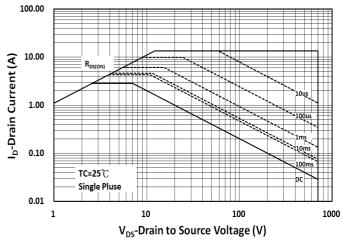
### BV<sub>DSS</sub> vs. Junction Temperature



### Maximum Safe Operating Area (DPAK/IPAK)



### **Maximum Safe Operating Area (ITO-220)**

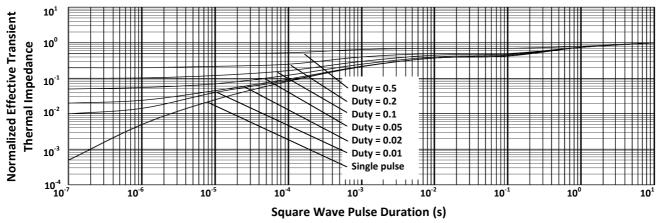




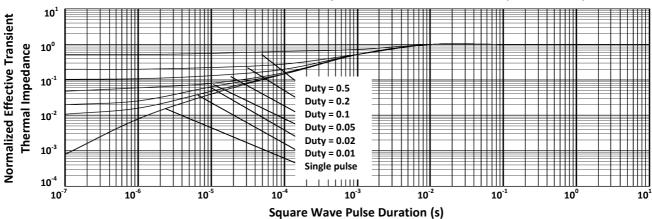
### **ELECTRICAL CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 



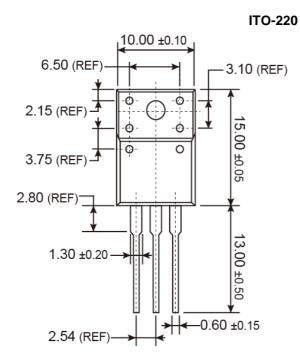


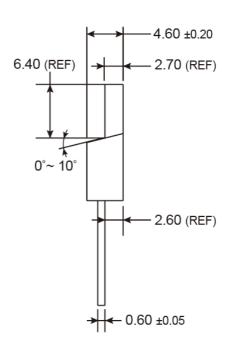
### Normalized Thermal Transient Impedance, Junction-to-Case (DPAK/IPAK)



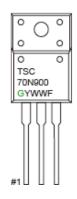


## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)





### **MARKING DIAGRAM**



**G** = Halogen Free

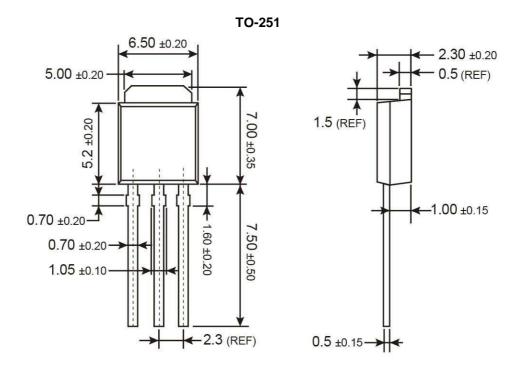
Y = Year Code

**WW** = Week Code (01~52)

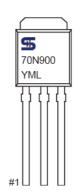
**F** = Factory Code



### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



### **MARKING DIAGRAM**



Y = Year Code

**M** = Month Code for Halogen Free Product

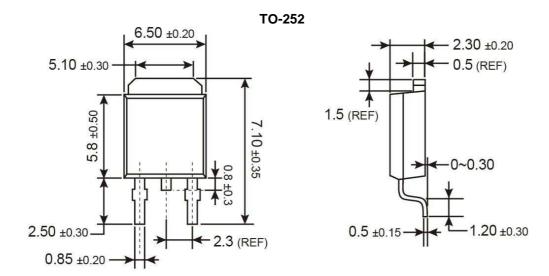
 $\mathbf{O}$  =Jan  $\mathbf{P}$  =Feb  $\mathbf{Q}$  =Mar  $\mathbf{R}$  =Apr

 $S = May \quad T = Jun \quad U = Jul \quad V = Aug$ 

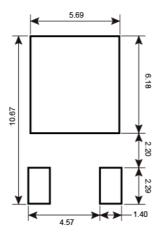
W = Sep X = Oct Y = Nov Z = DecL = Lot Code (1~9, A~Z)



# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



### SUGGESTED PAD LAYOUT (Unit: Millimeters)



### **MARKING DIAGRAM**



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

 $L = \text{Lot Code } (1\sim9, A\sim Z)$ 





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